

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# MT6L57AFS

## VHF~UHF Band Low-Noise Amplifier Applications

Two devices are incorporated in a fine-pitch, small-mold package (6 pins): fS6.

- Superior noise characteristics
- Superior performance in buffer and oscillator applications.

## Mounted Devices

	Q1	Q2
Corresponding three-pin products: TESM(fSM) mold products	MT3S06T (MT3S06FS)	MT3S04AT (MT3S04AFS)

### Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating		Unit
		Q1	Q2	
Collector- base voltage	V <sub>CBO</sub>	10	10	V
Collector- emitter voltage	V <sub>CEO</sub>	5	5	V
Emitter- base voltage	V <sub>EBO</sub>	1.5	2	V
Collector current	I <sub>C</sub>	15	40	mA
Base current	I <sub>B</sub>	7	10	mA
Collector power dissipation	P <sub>C</sub> (Note 1)	100		mW
		110 (Note 2)		
Junction temperature	T <sub>j</sub>	125		°C
Storage temperature range	T <sub>stg</sub>	−55~125		°C

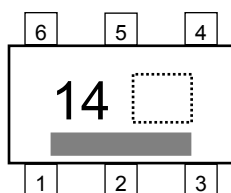
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

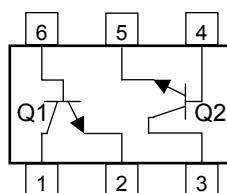
Note 1:  $10 \text{ mm}^2 \times 1.0 \text{ mm (t)}$ , mounted on a glass-epoxy printed circuit board.

Note 2: During two-element operation

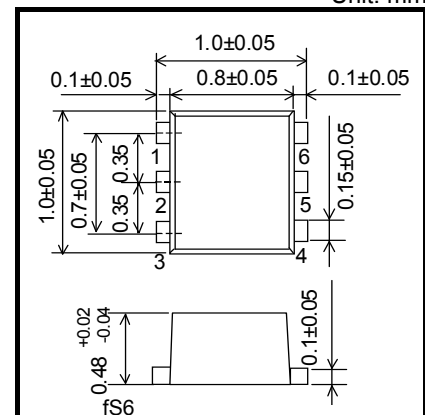
### Marking (top view)



### Pin Assignment (top view)



Unit: mm



1. Collector1 (C1)
2. Emitter1 (E1)
3. Collector2 (C2)
4. Base2 (B2)
5. Emitter2 (E2)
6. Base1 (B1)

JEDEC	—
JEIAJ	—
Toshiba	2-1F1A

Weight: 0.001g (typ.)

**Electrical Characteristics Q1 (Ta = 25°C)**

Characteristic	Symbol	Condition	Min	Typ.	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 5 \text{ V}, I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 1 \text{ V}, I_C = 0$	—	—	1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}$	70	—	140	
Reverse transfer capacitance	$C_{re}(\text{Note})$	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	0.25	0.5	pF
Transition frequency	$f_T$	$V_{CE} = 3 \text{ V}, I_C = 5 \text{ mA}$	7	10	—	GHz
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	8.5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 3 \text{ V}, I_C = 7 \text{ mA}, f = 2 \text{ GHz}$	7	9.5	—	
Noise figure	NF	$V_{CE} = 1 \text{ V}, I_C = 3 \text{ mA}, f = 2 \text{ GHz}$	—	1.7	3	dB

**Electrical Characteristics Q2 (Ta = 25°C)**

Characteristic	Symbol	Condition	Min	Typ.	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 5 \text{ V}, I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 1 \text{ V}, I_C = 0$	—	—	1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}$	80	—	160	
Reverse transfer capacitance	$C_{re}(\text{Note})$	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	0.8	1.05	pF
Transition frequency	$f_T$	$V_{CE} = 3 \text{ V}, I_C = 7 \text{ mA}$	5	7	—	GHz
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 1 \text{ GHz}$	—	9.5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 3 \text{ V}, I_C = 20 \text{ mA}, f = 1 \text{ GHz}$	10.5	13	—	
Noise figure	NF	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 1 \text{ GHz}$	—	1.3	2.2	dB

Note:  $C_{re}$  is measured with a three-terminal method using a capacitance bridge.

**Caution**

This device is sensitive to electrostatic discharge. Ensure that tools and equipment are sufficiently grounded before handling. When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

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20070701-EN GENERAL

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